

### Final datasheet

### High speed and low saturation voltage 750 V TRENCHSTOP™ IGBT7 technology co-packed with soft and fast recovery Emitter Controlled 7 diode

#### Features

- $V_{CE} = 750\text{ V}$
- $I_C = 100\text{ A}$
- Low switching losses
- Very low collector-emitter saturation voltage  $V_{CEsat}$
- Very soft, fast recovery antiparallel diode
- Smooth switching behavior
- Humidity robustness
- Optimized for hard switching, two- and three-level topologies
- Complete product spectrum and PSpice Models: <http://www.infineon.com/igbt/>

#### Potential applications

- Industrial UPS
- EV Charging
- String inverter
- Energy storage systems (ESS)

#### Product validation

- Qualified for industrial applications according to the relevant tests of JEDEC47/20/22

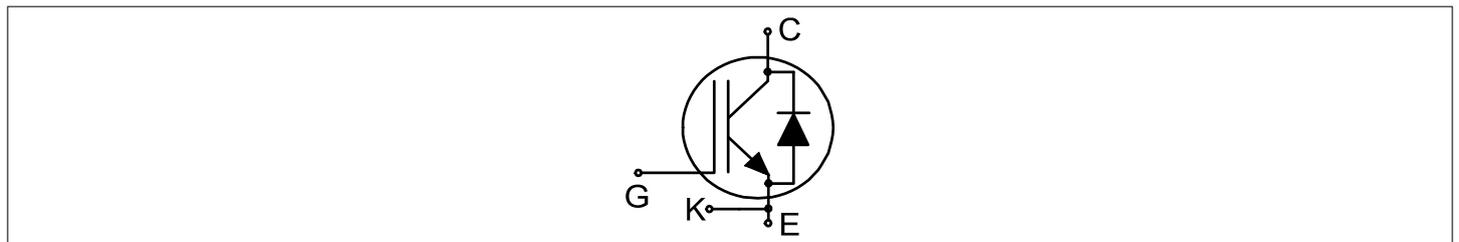


- Lead-free
- Green
- Halogen-free
- RoHS

#### Description

Package pin definition:

- Pin C & backside – Collector
- Pin E – Emitter
- Pin K – Kelvin emitter
- Pin G – Gate



Type	Package	Marking
IKZA100N75EH7	PG-TO247-4-U02	K100GEH7

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## 1 Package

**Table 1 Characteristic values**

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Internal emitter inductance measured 5 mm (0.197 in.) from case	$L_E$			13		nH
Storage temperature	$T_{stg}$		-55		150	°C
Soldering temperature	$T_{sold}$	wave soldering 1.6 mm (0.063 in.) from case for 10 s			260	°C
Mounting torque	$M$	M3 screw, Maximum of mounting processes: 3			0.6	Nm
Thermal resistance, junction-ambient	$R_{th(j-a)}$				40	K/W
IGBT thermal resistance, junction-case	$R_{th(j-c)}$			0.27	0.35	K/W
Diode thermal resistance, junction-case	$R_{th(j-c)}$			0.36	0.47	K/W

## 2 IGBT

**Table 2 Maximum rated values**

Parameter	Symbol	Note or test condition	Values	Unit	
Collector-emitter voltage	$V_{CE}$	$T_{vj} \geq 25 \text{ °C}$	750	V	
DC collector current, limited by $T_{vjmax}$	$I_C$	limited by bondwire	$T_c = 25 \text{ °C}$	140	A
			$T_c = 100 \text{ °C}$	122	
Pulsed collector current, $t_p$ limited by $T_{vjmax}$	$I_{Cpulse}$		400	A	
Turn-off safe operating area		$V_{CE} \leq 750 \text{ V}, t_p \leq 1 \text{ }\mu\text{s}, T_{vj} \leq 175 \text{ °C}$	400	A	
Gate-emitter voltage	$V_{GE}$		$\pm 20$	V	
Transient gate-emitter voltage	$V_{GE}$	$t_p \leq 10 \text{ }\mu\text{s}, D < 0.01$	$\pm 30$	V	
Power dissipation	$P_{tot}$		$T_c = 25 \text{ °C}$	429	W
			$T_c = 100 \text{ °C}$	214	

**Table 3 Characteristic values**

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Collector-emitter saturation voltage	$V_{CEsat}$	$I_C = 100\text{ A}, V_{GE} = 15\text{ V}$	$T_{vj} = 25\text{ °C}$		1.45	1.75	V
			$T_{vj} = 175\text{ °C}$		1.75		
Gate-emitter threshold voltage	$V_{GEth}$	$I_C = 0.88\text{ mA}, V_{CE} = V_{GE}$		3.2	4	4.8	V
Zero gate-voltage collector current	$I_{CES}$	$V_{CE} = 750\text{ V}, V_{GE} = 0\text{ V}$	$T_{vj} = 25\text{ °C}$			30	$\mu\text{A}$
			$T_{vj} = 175\text{ °C}$		3000		
Gate-emitter leakage current	$I_{GES}$	$V_{CE} = 0\text{ V}, V_{GE} = 20\text{ V}$				100	nA
Transconductance	$g_{fs}$	$I_C = 100\text{ A}, V_{CE} = 20\text{ V}$			140		S
Input capacitance	$C_{ies}$	$V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}, f = 100\text{ kHz}$			5160		pF
Output capacitance	$C_{oes}$	$V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}, f = 100\text{ kHz}$			148		pF
Reverse transfer capacitance	$C_{res}$	$V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}, f = 100\text{ kHz}$			19		pF
Gate charge	$Q_G$	$V_{CC} = 600\text{ V}, I_C = 100\text{ A}, V_{GE} = 15\text{ V}$			205		nC
Turn-on delay time	$t_{d(on)}$	$V_{CC} = 400\text{ V}, V_{GE} = 0/15\text{ V}, R_{G(on)} = 10\ \Omega, R_{G(off)} = 10\ \Omega$	$T_{vj} = 25\text{ °C}, I_C = 100\text{ A}$		30		ns
			$T_{vj} = 175\text{ °C}, I_C = 100\text{ A}$		29		
Rise time (inductive load)	$t_r$	$V_{CC} = 400\text{ V}, V_{GE} = 0/15\text{ V}, R_{G(on)} = 10\ \Omega, R_{G(off)} = 10\ \Omega$	$T_{vj} = 25\text{ °C}, I_C = 100\text{ A}$		16		ns
			$T_{vj} = 175\text{ °C}, I_C = 100\text{ A}$		19		
Turn-off delay time	$t_{d(off)}$	$V_{CC} = 400\text{ V}, V_{GE} = 0/15\text{ V}, R_{G(on)} = 10\ \Omega, R_{G(off)} = 10\ \Omega$	$T_{vj} = 25\text{ °C}, I_C = 100\text{ A}$		238		ns
			$T_{vj} = 175\text{ °C}, I_C = 100\text{ A}$		273		
Fall time (inductive load)	$t_f$	$V_{CC} = 400\text{ V}, V_{GE} = 0/15\text{ V}, R_{G(on)} = 10\ \Omega, R_{G(off)} = 10\ \Omega$	$T_{vj} = 25\text{ °C}, I_C = 100\text{ A}$		21		ns
			$T_{vj} = 175\text{ °C}, I_C = 100\text{ A}$		62		
Turn-on energy	$E_{on}$	$V_{CC} = 400\text{ V}, V_{GE} = 0/15\text{ V}, R_{G(on)} = 10\ \Omega, R_{G(off)} = 10\ \Omega$	$T_{vj} = 25\text{ °C}, I_C = 100\text{ A}$		1.7		mJ
			$T_{vj} = 175\text{ °C}, I_C = 100\text{ A}$		2.2		

**(table continues...)**

**Table 3 (continued) Characteristic values**

Parameter	Symbol	Note or test condition	Values			Unit	
			Min.	Typ.	Max.		
Turn-off energy	$E_{off}$	$V_{CC} = 400\text{ V}, V_{GE} = 0/15\text{ V},$ $R_{G(on)} = 10\ \Omega,$ $R_{G(off)} = 10\ \Omega$	$T_{vj} = 25\text{ }^\circ\text{C},$ $I_C = 100\text{ A}$		1.2		mJ
			$T_{vj} = 175\text{ }^\circ\text{C},$ $I_C = 100\text{ A}$		2.3		
Total switching energy	$E_{ts}$	$V_{CC} = 400\text{ V}, V_{GE} = 0/15\text{ V},$ $R_{G(on)} = 10\ \Omega,$ $R_{G(off)} = 10\ \Omega$	$T_{vj} = 25\text{ }^\circ\text{C},$ $I_C = 100\text{ A}$		2.9		mJ
			$T_{vj} = 175\text{ }^\circ\text{C},$ $I_C = 100\text{ A}$		4.6		
Operating junction temperature	$T_{vj}$		-40		175	$^\circ\text{C}$	

### 3 Diode

**Table 4 Maximum rated values**

Parameter	Symbol	Note or test condition	Values	Unit	
Diode forward current, limited by $T_{vjmax}$	$I_F$	limited by bondwire	$T_c = 25\text{ }^\circ\text{C}$	140	A
			$T_c = 100\text{ }^\circ\text{C}$	104	
Diode pulsed current, $t_p$ limited by $T_{vjmax}$	$I_{Fpulse}$		400	A	
Power dissipation	$P_{tot}$		$T_c = 25\text{ }^\circ\text{C}$	319	W
			$T_c = 100\text{ }^\circ\text{C}$	160	

**Table 5 Characteristic values**

Parameter	Symbol	Note or test condition	Values			Unit	
			Min.	Typ.	Max.		
Diode forward voltage	$V_F$	$I_F = 100\text{ A}$	$T_{vj} = 25\text{ }^\circ\text{C}$		1.65	2	V
			$T_{vj} = 175\text{ }^\circ\text{C}$		1.6		
Diode reverse recovery time	$t_{rr}$	$V_R = 400\text{ V}, R_{G(on)} = 10\ \Omega$	$T_{vj} = 25\text{ }^\circ\text{C},$ $I_F = 100\text{ A}$		90		ns
			$T_{vj} = 175\text{ }^\circ\text{C},$ $I_F = 100\text{ A}$		171		
Diode reverse recovery charge	$Q_{rr}$	$V_R = 400\text{ V}, R_{G(on)} = 10\ \Omega$	$T_{vj} = 25\text{ }^\circ\text{C},$ $I_F = 100\text{ A}$		3.6		$\mu\text{C}$
			$T_{vj} = 175\text{ }^\circ\text{C},$ $I_F = 100\text{ A}$		8.9		

(table continues...)

**Table 5 (continued) Characteristic values**

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Diode peak reverse recovery current	$I_{rrm}$	$V_R = 400\text{ V}, R_{G(on)} = 10\ \Omega$	$T_{vj} = 25\ ^\circ\text{C}, I_F = 100\text{ A}$		75.5	A
			$T_{vj} = 175\ ^\circ\text{C}, I_F = 100\text{ A}$		115.9	
Diode peak rate of fall of reverse recovery current	$di_{rr}/dt$	$V_R = 400\text{ V}, R_{G(on)} = 10\ \Omega$	$T_{vj} = 25\ ^\circ\text{C}, I_F = 100\text{ A}$		-1020	A/ $\mu\text{s}$
			$T_{vj} = 175\ ^\circ\text{C}, I_F = 100\text{ A}$		-785	
Reverse recovery energy	$E_{rec}$	$V_R = 400\text{ V}, R_{G(on)} = 10\ \Omega$	$T_{vj} = 25\ ^\circ\text{C}, I_F = 100\text{ A}$		0.92	mJ
			$T_{vj} = 175\ ^\circ\text{C}, I_F = 100\text{ A}$		2.57	
Operating junction temperature	$T_{vj}$			-40	175	$^\circ\text{C}$

**Note:** For optimum lifetime and reliability, Infineon recommends operating conditions that do not exceed 80% of the maximum ratings stated in this datasheet.

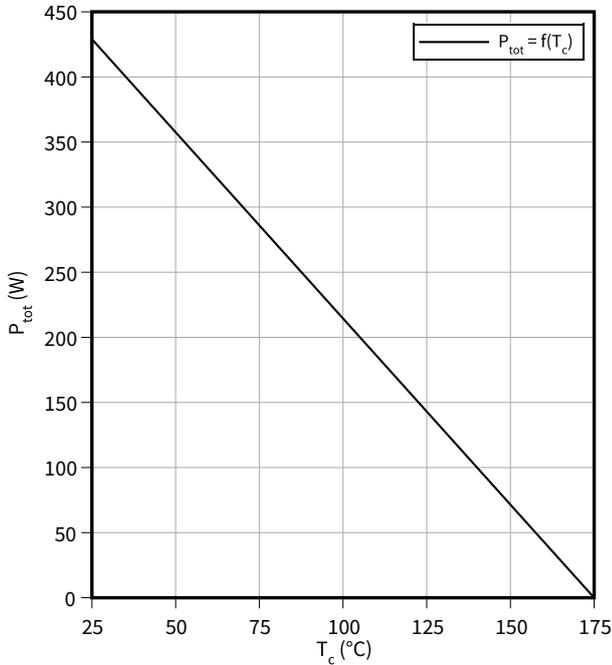
Electrical Characteristic, at  $T_{vj} = 25\ ^\circ\text{C}$ , unless otherwise specified.

Dynamic test circuit, parasitic inductance  $L_\sigma = 8\text{ nH}$ , parasitic capacitor  $C_\sigma = 30\text{ pF}$  from Fig. E. Energy losses include “tail” and diode reverse recovery.

## 4 Characteristics diagrams

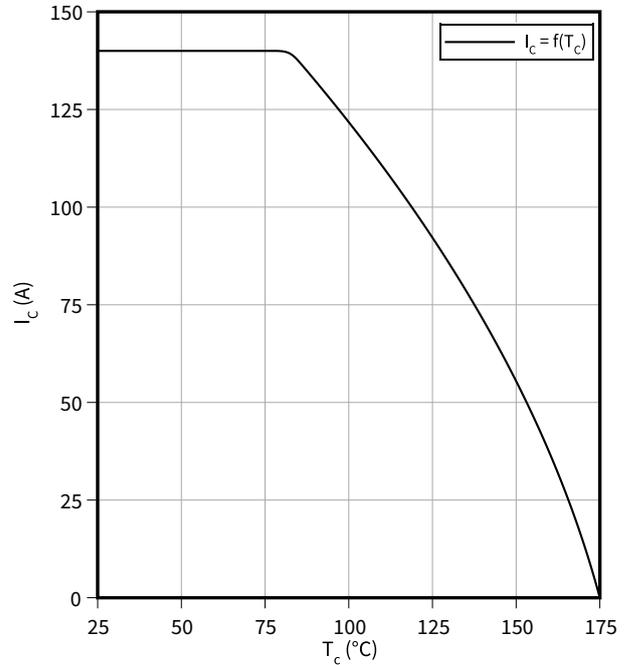
### Power dissipation as a function of case temperature

$P_{tot} = f(T_c)$   
 $T_{vj} \leq 175\text{ °C}$



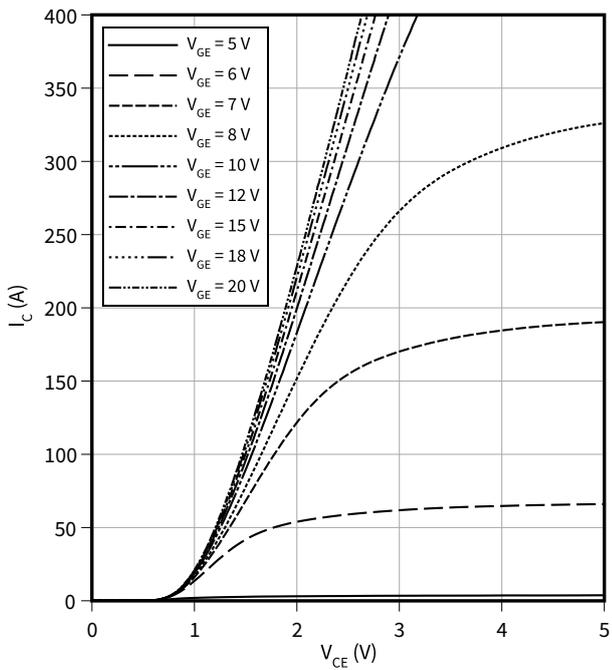
### Collector current as a function of case temperature

$I_C = f(T_c)$   
 $T_{vj} \leq 175\text{ °C}, V_{GE} \geq 15\text{ V}$



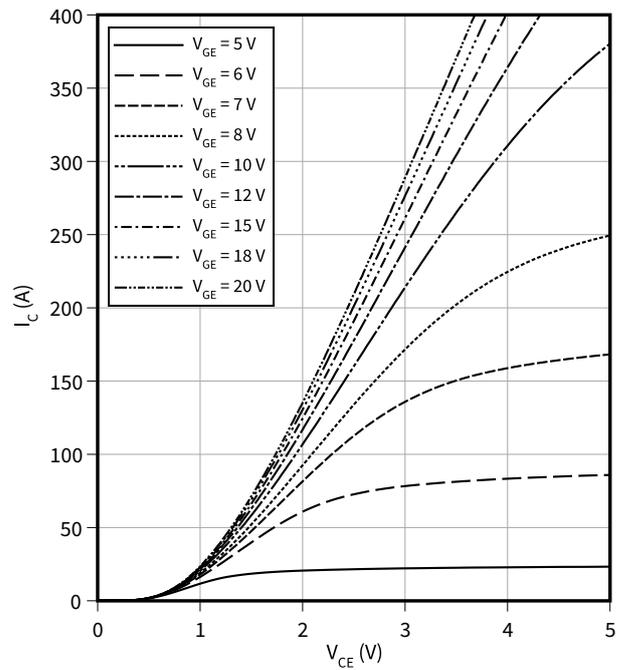
### Typical output characteristic

$I_C = f(V_{CE})$   
 $T_{vj} = 25\text{ °C}$



### Typical output characteristic

$I_C = f(V_{CE})$   
 $T_{vj} = 175\text{ °C}$

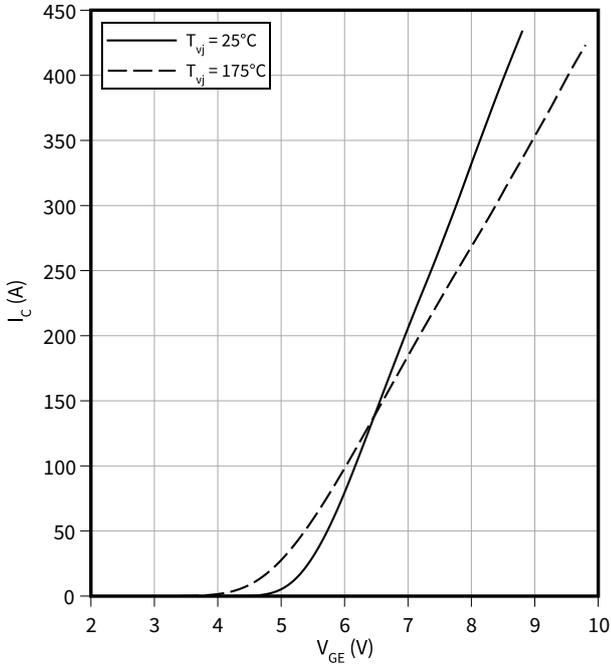


**4 Characteristics diagrams**

**Typical transfer characteristic**

$I_C = f(V_{GE})$

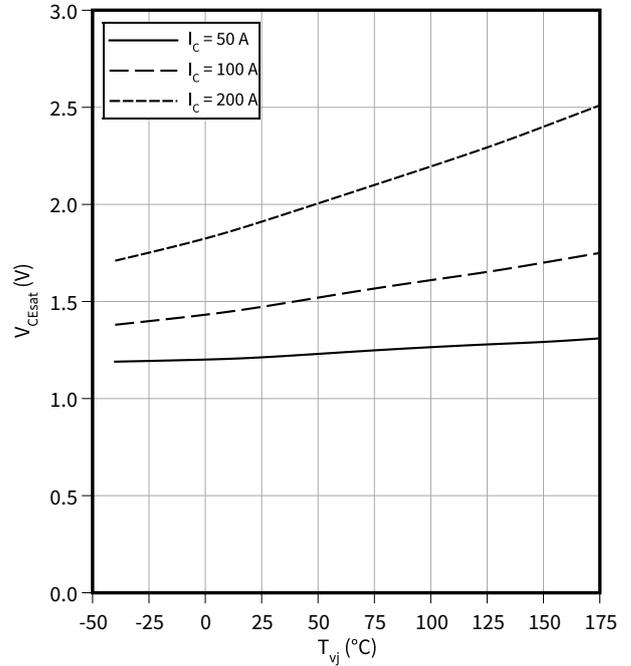
$V_{CE} = 20\text{ V}$



**Typical collector-emitter saturation voltage as a function of junction temperature**

$V_{CEsat} = f(T_{vj})$

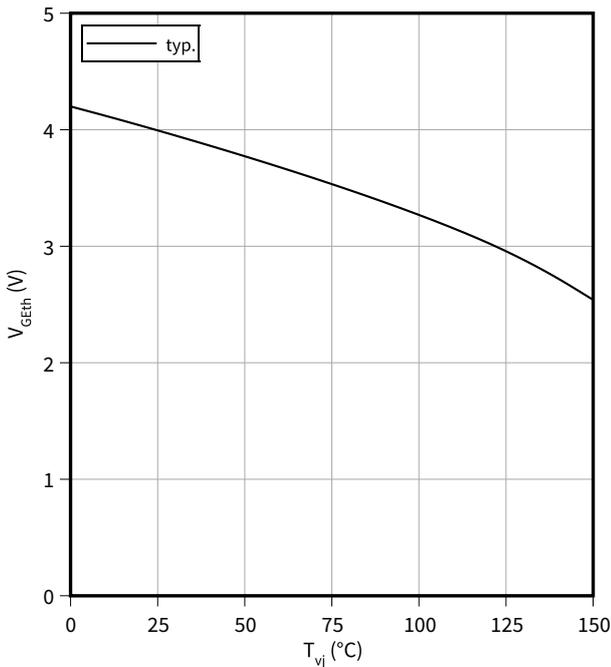
$V_{GE} = 15\text{ V}$



**Gate-emitter threshold voltage as a function of junction temperature**

$V_{GEth} = f(T_{vj})$

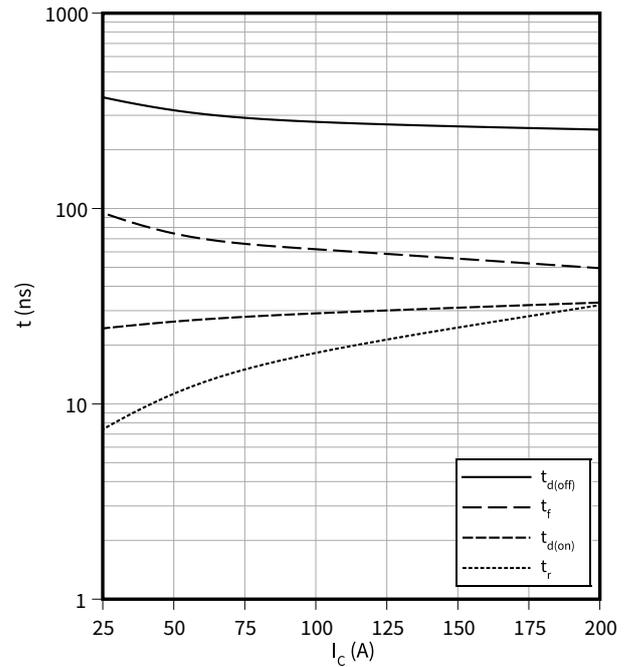
$I_C = 0.88\text{ mA}$



**Typical switching times as a function of collector current**

$t = f(I_C)$

$V_{CC} = 400\text{ V}, T_{vj} = 175^\circ\text{C}, V_{GE} = 0/15\text{ V}, R_G = 10\ \Omega$

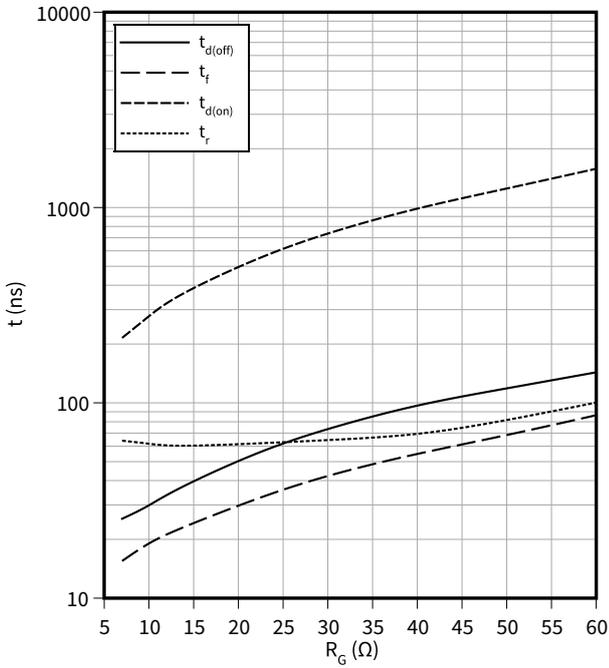


4 Characteristics diagrams

Typical switching times as a function of gate resistor

$t = f(R_G)$

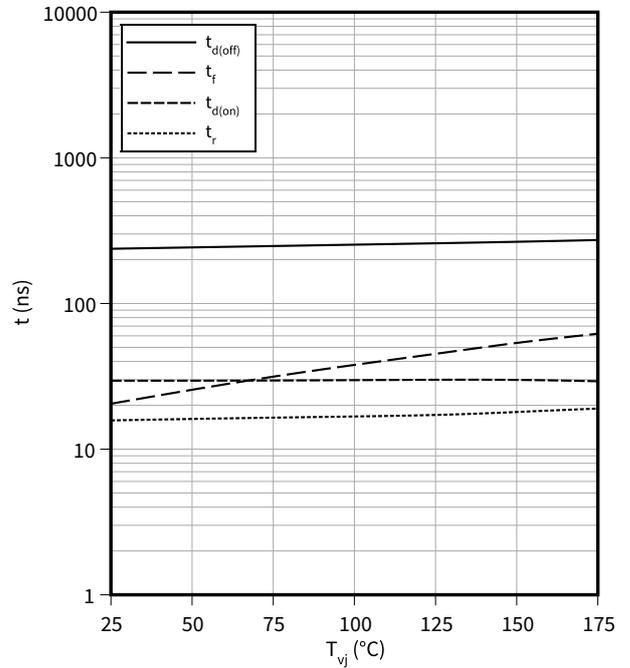
$I_C = 100\text{ A}$ ,  $V_{CC} = 400\text{ V}$ ,  $T_{vj} = 175\text{ °C}$ ,  $V_{GE} = 0/15\text{ V}$



Typical switching times as a function of junction temperature

$t = f(T_{vj})$

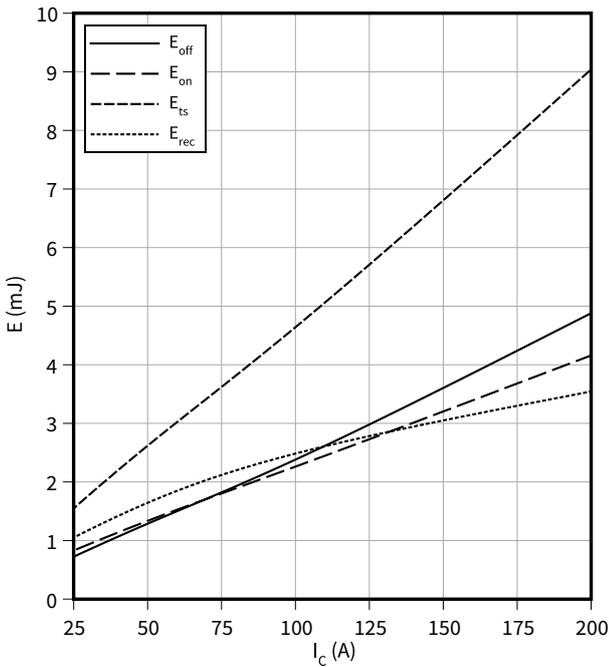
$I_C = 100\text{ A}$ ,  $V_{CC} = 400\text{ V}$ ,  $V_{GE} = 0/15\text{ V}$ ,  $R_G = 10\text{ Ω}$



Typical switching energy losses as a function of collector current

$E = f(I_C)$

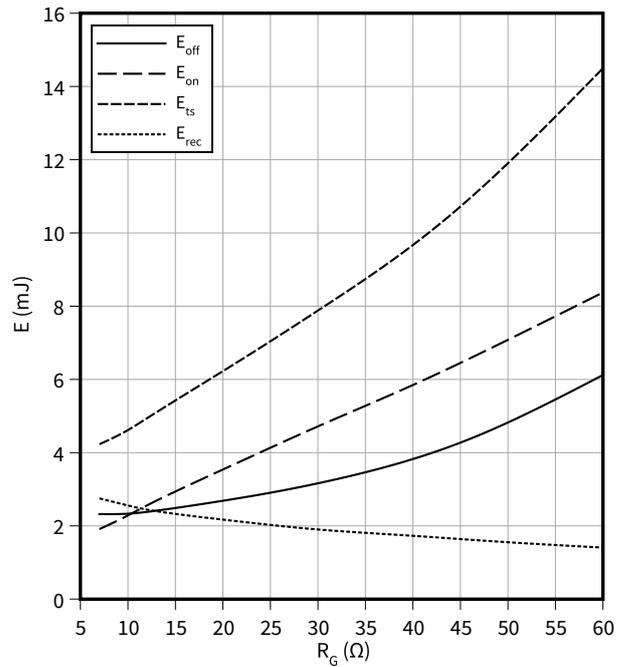
$V_{CC} = 400\text{ V}$ ,  $T_{vj} = 175\text{ °C}$ ,  $V_{GE} = 0/15\text{ V}$ ,  $R_G = 10\text{ Ω}$



Typical switching energy losses as a function of gate resistor

$E = f(R_G)$

$I_C = 100\text{ A}$ ,  $V_{CC} = 400\text{ V}$ ,  $T_{vj} = 175\text{ °C}$ ,  $V_{GE} = 0/15\text{ V}$

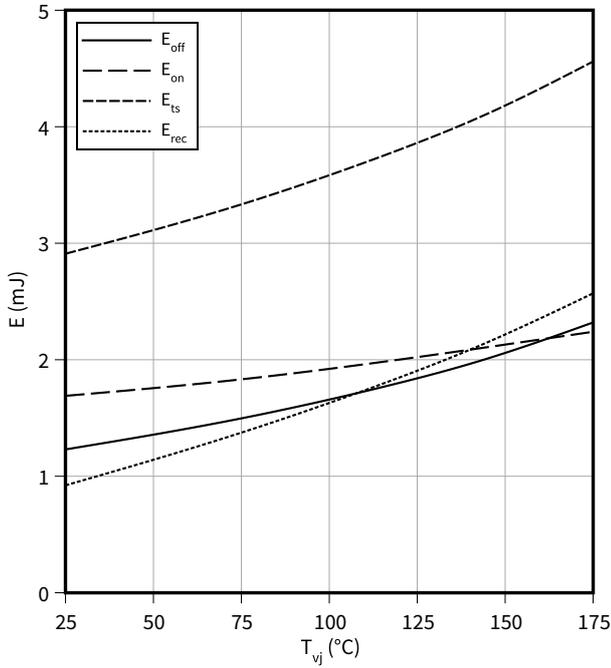


4 Characteristics diagrams

**Typical switching energy losses as a function of junction temperature**

$E = f(T_{vj})$

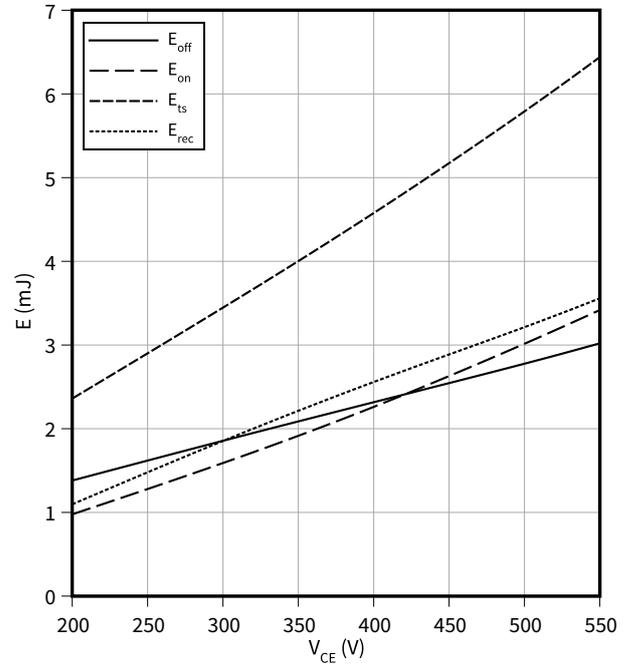
$I_C = 100\text{ A}$ ,  $V_{CC} = 400\text{ V}$ ,  $V_{GE} = 0/15\text{ V}$ ,  $R_G = 10\ \Omega$



**Typical switching energy losses as a function of collector emitter voltage**

$E = f(V_{CE})$

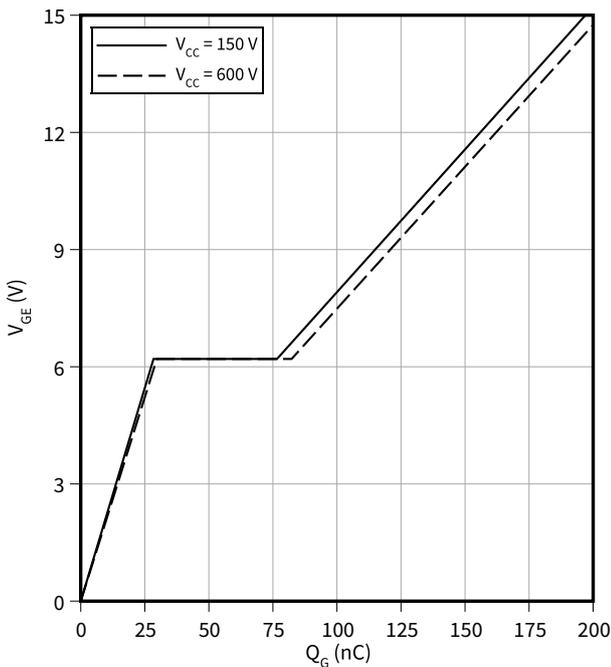
$V_{GE} = 0/15\text{ V}$ ,  $R_G = 10\ \Omega$ ,  $I_C = 100\text{ A}$ ,  $T_{vj} = 175\text{ °C}$



**Typical gate charge**

$V_{GE} = f(Q_G)$

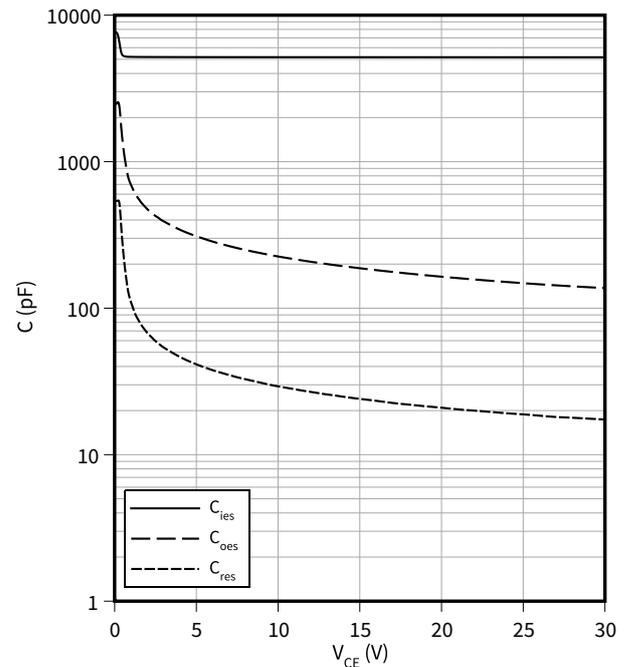
$I_C = 100\text{ A}$



**Typical capacitance as a function of collector-emitter voltage**

$C = f(V_{CE})$

$f = 100\text{ kHz}$ ,  $V_{GE} = 0\text{ V}$

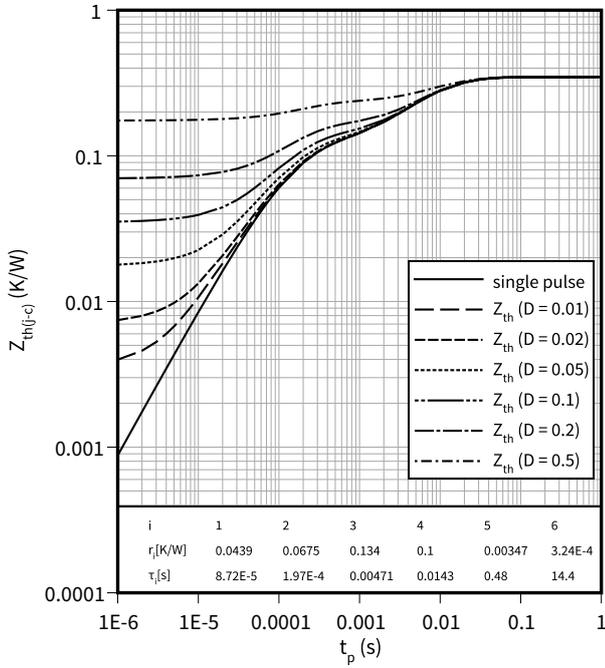


4 Characteristics diagrams

**IGBT transient thermal impedance as a function of pulse width**

$$Z_{th(j-c)} = f(t_p)$$

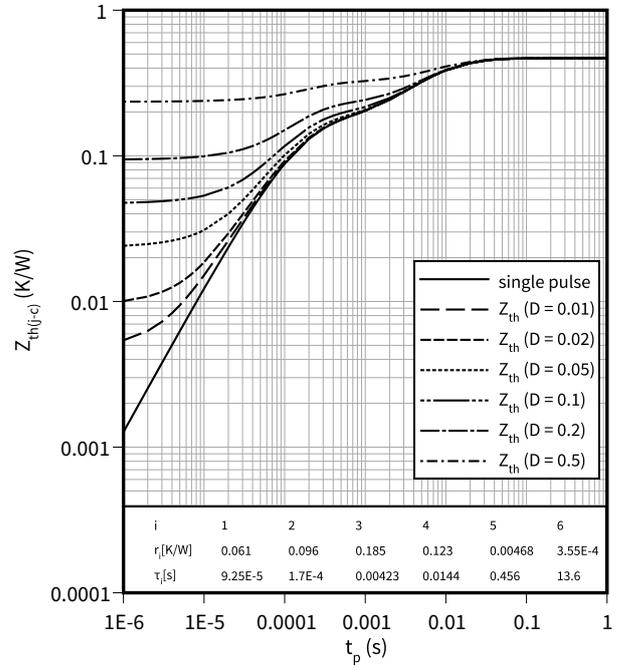
$$D = t_p/T$$



**Diode transient thermal impedance as a function of pulse width**

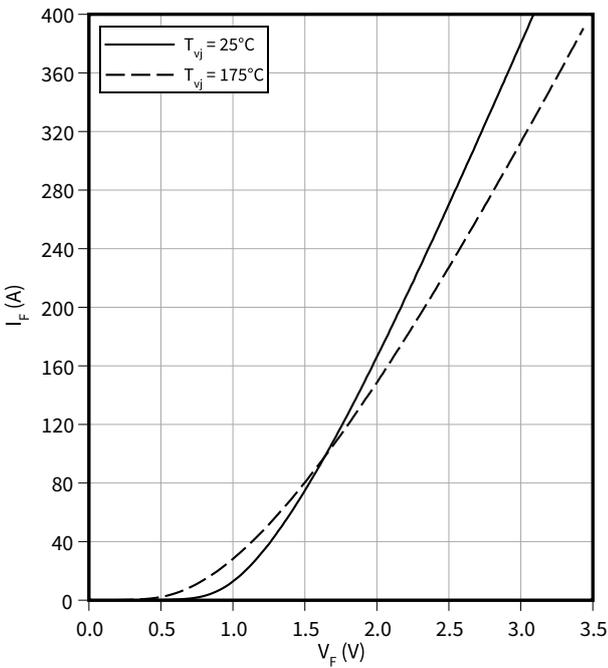
$$Z_{th(j-c)} = f(t_p)$$

$$D = t_p/T$$



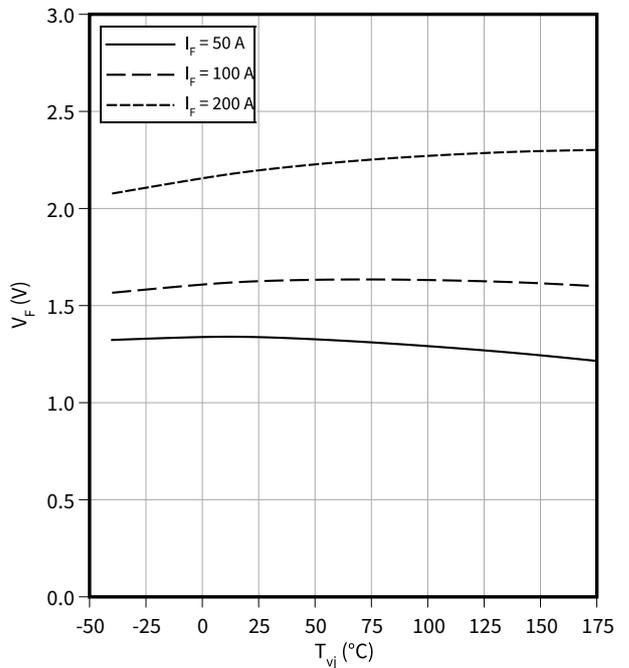
**Typical diode forward current as a function of forward voltage**

$$I_F = f(V_F)$$



**Typical diode forward voltage as a function of junction temperature**

$$V_F = f(T_{vj})$$

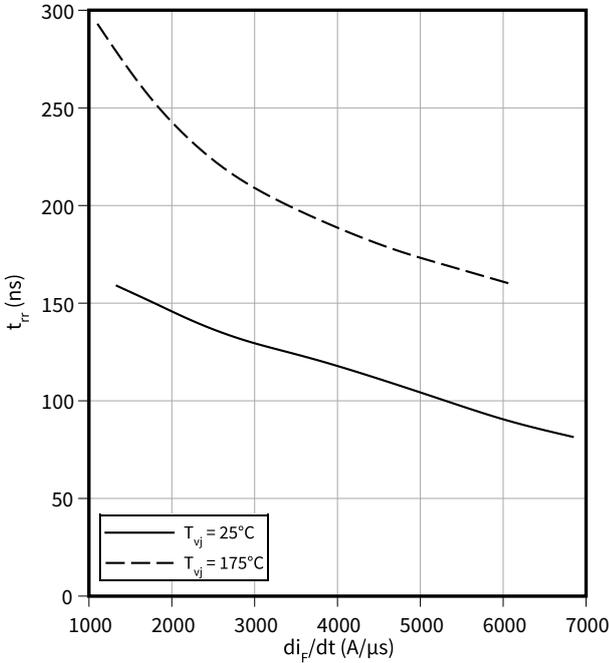


4 Characteristics diagrams

**Typical reverse recovery time as a function of diode current slope**

$t_{rr} = f(di_F/dt)$

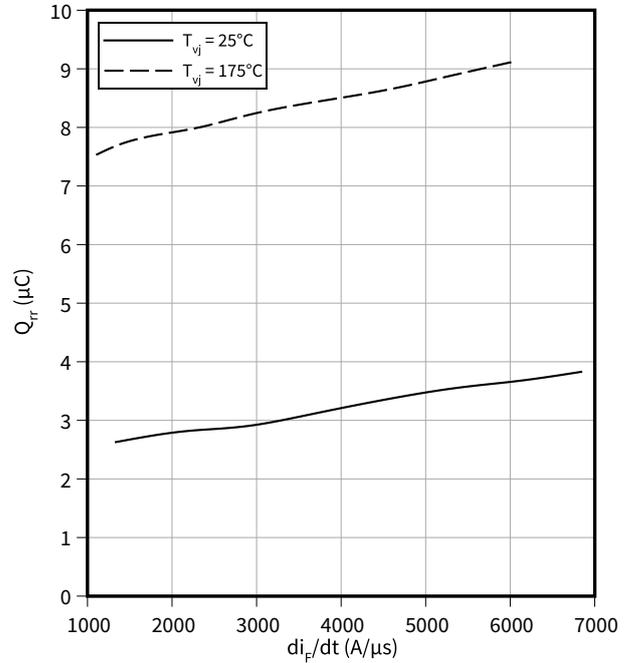
$V_R = 400\text{ V}, I_F = 100\text{ A}$



**Typical reverse recovery charge as a function of diode current slope**

$Q_{rr} = f(di_F/dt)$

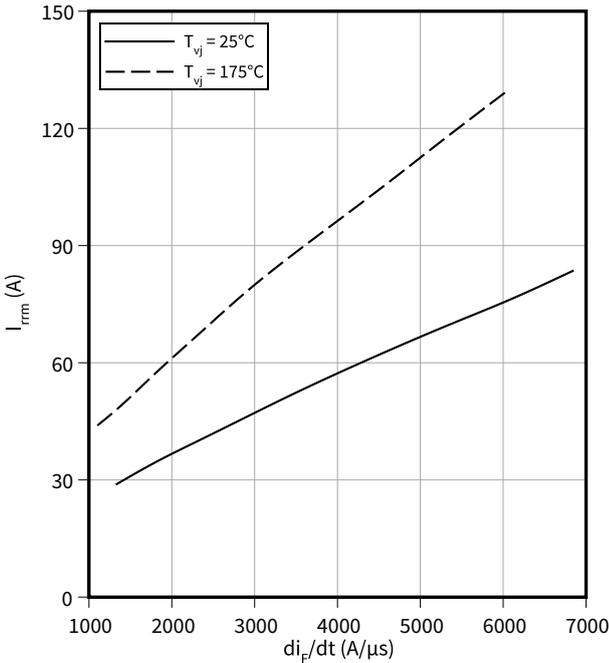
$V_R = 400\text{ V}, I_F = 100\text{ A}$



**Typical reverse recovery current as a function of diode current slope**

$I_{rrm} = f(di_F/dt)$

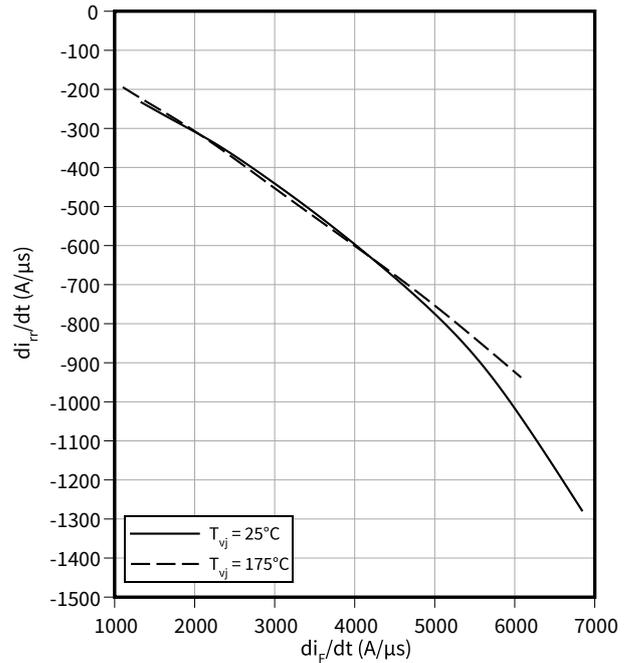
$V_R = 400\text{ V}, I_F = 100\text{ A}$



**Typical diode peak rate of fall of reverse recovery current as a function of diode current slope**

$di_{rr}/dt = f(di_F/dt)$

$V_R = 400\text{ V}, I_F = 100\text{ A}$

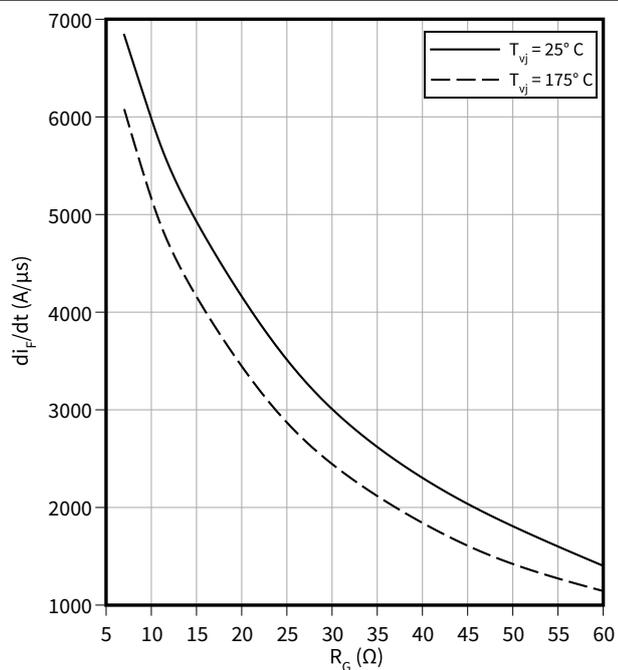


**4 Characteristics diagrams**

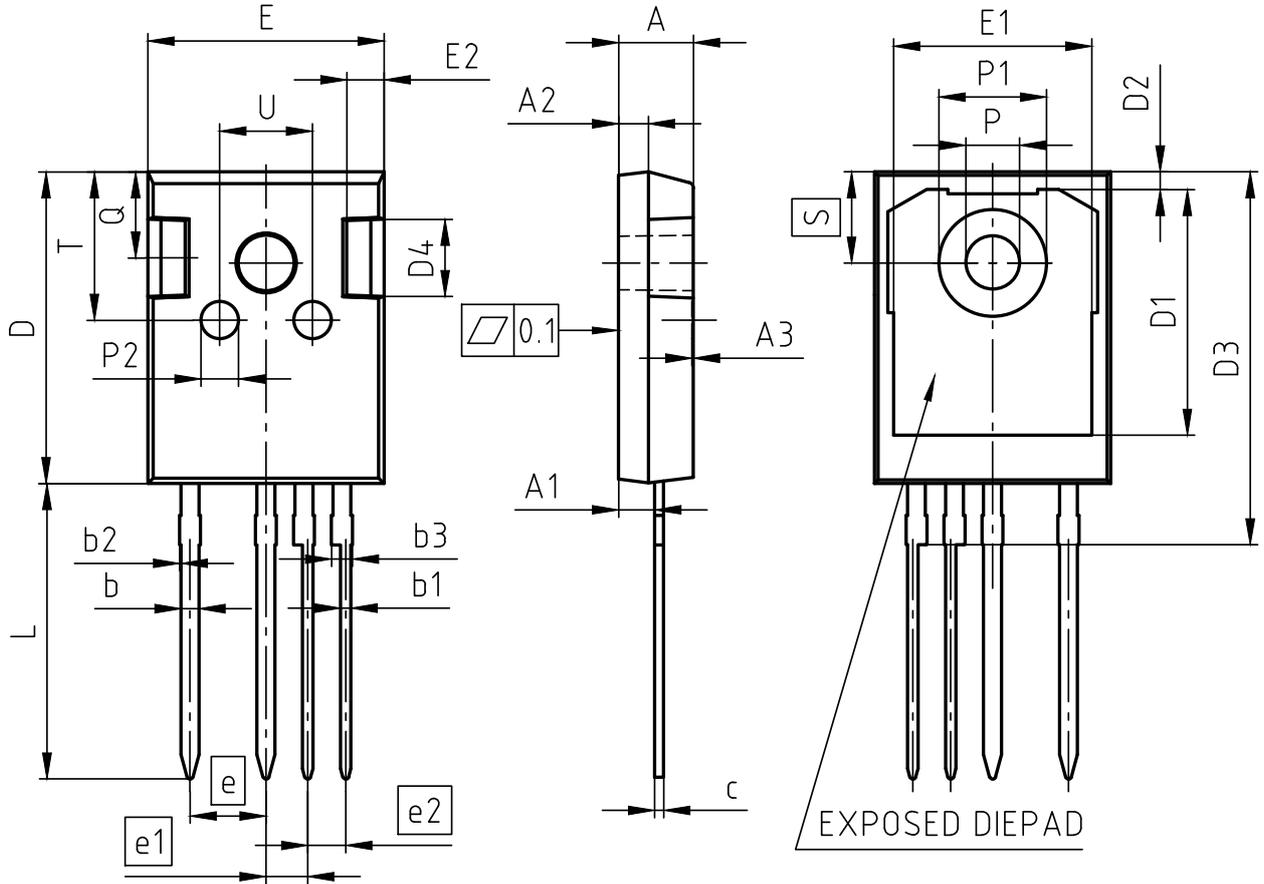
**Typical diode current slope as a function of gate resistor**

$di_F/dt = f(R_G)$

$V_R = 400\text{ V}, I_F = 100\text{ A}$



5 Package outlines



NOTES:  
 ALL DIMENSIONS DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS.

PACKAGE - GROUP NUMBER:		PG-TO247-4-U02			
DIMENSIONS	MILLIMETERS		DIMENSIONS	MILLIMETERS	
	MIN.	MAX.		MIN.	MAX.
A	4.90	5.10	E	15.70	15.90
A1	2.31	2.51	E1	13.10	13.50
A2	1.90	2.10	E2	2.40	2.60
A3	0.05	0.25	e	5.08	
b	1.10	1.30	e1	2.79	
b1	0.65	0.79	e2	2.54	
b2	---	0.20	N	4	
b3	1.34	1.44	L	19.80	20.10
c	0.58	0.66	øP	3.50	3.70
D	20.90	21.10	øP1	7.00	7.40
D1	16.25	16.85	øP2	2.40	2.60
D2	1.05	1.35	Q	5.60	6.00
D3	24.97	25.27	S	6.15	
D4	4.90	5.10	T	9.80	10.20
			U	6.00	6.40

Figure 1

6 Testing conditions

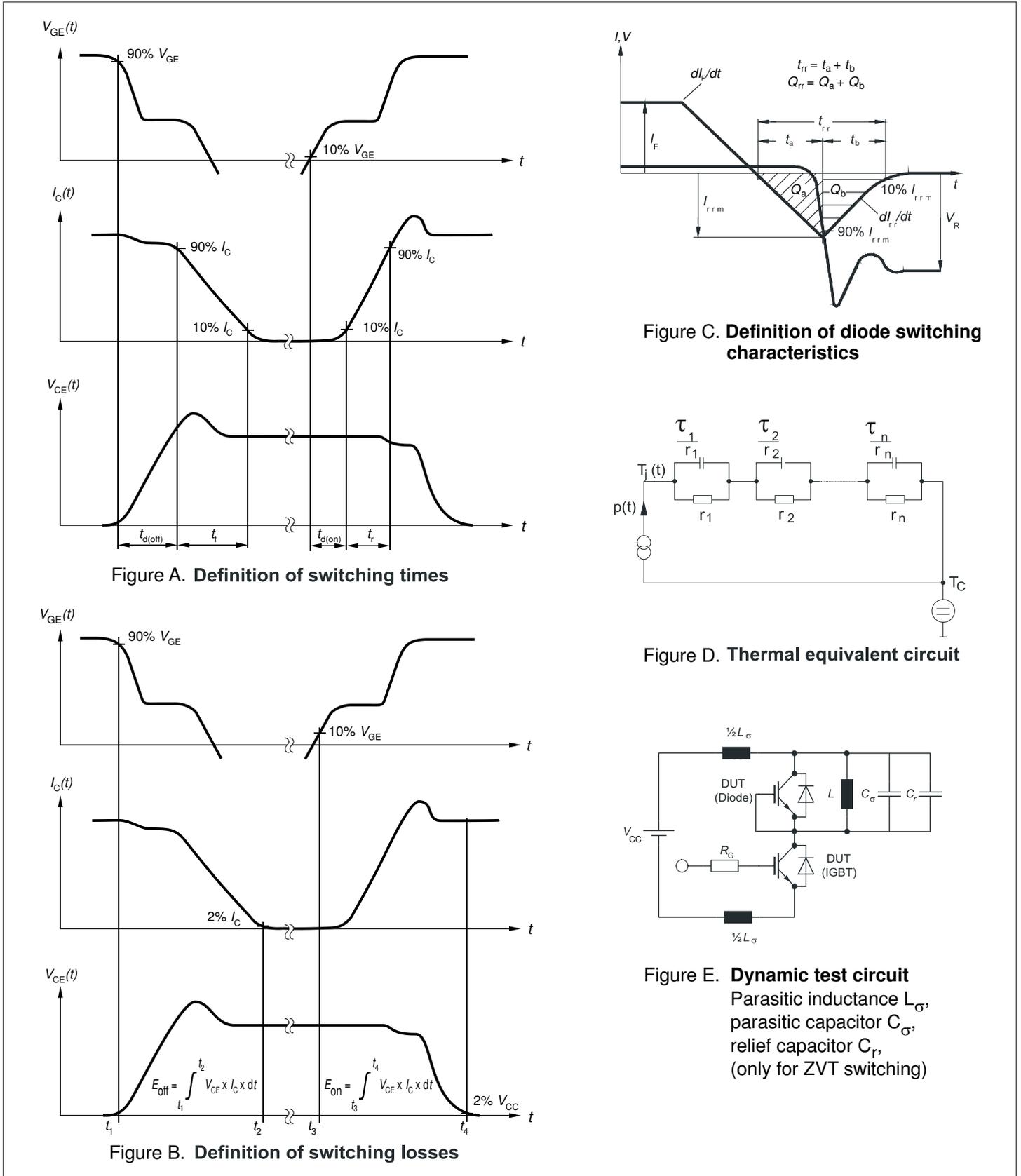


Figure 2

**Revision history**

<b>Document revision</b>	<b>Date of release</b>	<b>Description of changes</b>
0.10	2025-03-20	Preliminary datasheet
1.00	2025-07-31	Final datasheet

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